



DPLS350Y

50V PNP LOW SATURATION POWER TRANSISTOR IN SOT89

Features

- BV_{CEO} > -50V
- I_C = -3A High Continuous Collector Current
- I_{CM} up to -5A Peak Pulse Current
- 2W Power Dissipation
- Low Saturation Voltage V_{CE(sat)} < -180mV @ 1A
- $R_{CE(sat)} = 67m\Omega$ @ 2A for a Low Equivalent On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

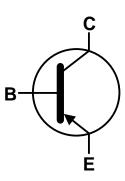
Case: SOT89

- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.052 grams (Approximate)

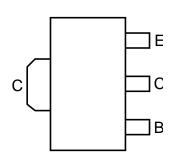
SOT89



Top View



Device Symbol



Top View Pin-Out

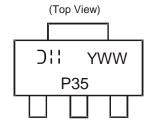
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DPLS350Y-13	P35	13	12	2,500
DPLS350Y-13R	P35	13	12	4,000
DPLS350YTC	P35	13	12	4,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- ${\it 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.}\\$

Marking Information



P35 = Product Type Marking Code: YWW = Date Code Marking Y = Last Digit of Year ex: 5 = 2015 WW = Week Code 01 - 53



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	I _{CM}	-5	Α
Base Current	I _B	-500	mA

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
	(Note 5)		1		
Power Dissipation	(Note 6)	P _D	1.6	W	
	(Note 7)		2.0		
	(Note 5)		125		
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{ heta JA}$	78	°C/W	
	(Note 7)		62.5	I	
Thermal Resistance, Junction to Lead	(Note 8)	$R_{\theta JL}$	5.7	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

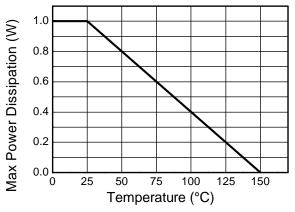
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

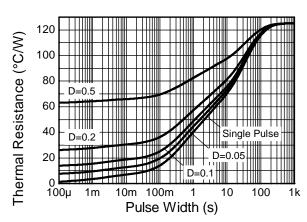
Notes:

- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



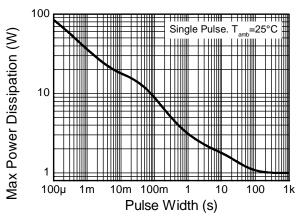
Thermal Characteristics and Derating Information



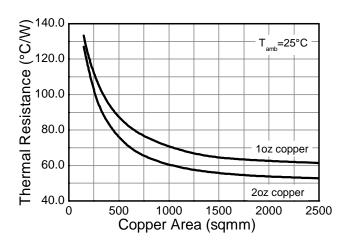


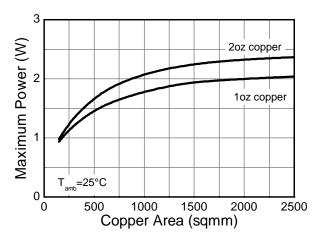
Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation





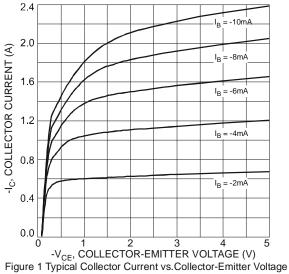


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	BV _{CBO}	-50	_	_	V	I _C = -100μA	
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-50	_	_	V	I _C = -10mA	
Emitter-Base Breakdown Voltage	BV _{EBO}	-6	_	_	V	$I_E = -100 \mu A$	
Collector-Emitter Cut-off Current	I _{CES}	_	_	-100	nA	V _{CE} = -50V	
Collector Cut-off Current	I _{CBO}	_	1	-100	nA	V _{CB} = -50V	
Collector Cut-on Current				-50	μA	V _{CB} = -50V, T _A = +150°C	
Emitter Cut-off Current	I _{EBO}	_	_	-100	nA	V _{EB} = -5V	
		200		_		I _C = -100mA, V _{CE} = -2V	
		200		_		I _C = -500mA, V _{CE} = -2V	
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	200	_	450	_	I _C = -1A, V _{CE} = -2V	
		130		_		I _C = -2A, V _{CE} = -2V	
		80		_		$I_C = -3A$, $V_{CE} = -2V$	
		_	_	-90	mV	I _C = -500mA, I _B = -50mA	
				-180		$I_C = -1A$, $I_B = -50mA$	
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}			-320		I _C = -2A, I _B = -100mA	
				-270		$I_C = -2A$, $I_B = -200mA$	
				-390		$I_C = -3A$, $I_B = -300mA$	
Equivalent On-Resistance	R _{CE(sat)}	1	67	135	mΩ	$I_C = -2A$, $I_B = -200mA$	
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_		-1.1	V	$I_C = -2A$, $I_B = -100mA$	
Base-Emilier Saturation voltage (Note 10)				-1.2		$I_C = -3A$, $I_B = -300mA$	
Base-Emitter Turn-On Current (Note 10)	V _{BE(on)}	1	_	-1.1	V	$I_C = -1A, V_{CE} = -2V$	
Transition Frequency	f⊤	100	_	-	MHz	$I_C = -100 \text{mA}, V_{CE} = -5 \text{V},$ f = 100 MHz	
Collector Output Capacitance	C _{obo}	_	_	35	pF	V _{CB} = -10V, I _E = 0, f = 1MHz	
Turn-On Time	t _(ON)	_	87	_	ns		
Delay Time	t _D	_	41	_	ns		
Rise Time	t _R	_	46	_	ns	$V_{CC} = -30v$,	
Turn-Off Time	t _(OFF)	_	294	_	ns	$I_{CC} = 150 \text{mA}$ $I_{B1} = I_{B2} = 15 \text{mA}$	
Storage Time	ts	_	250	_	ns	- 182 = 13111A	
Fall Time	t _F	_	44	_	ns		

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.





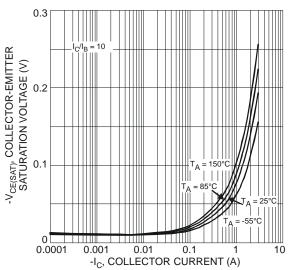


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

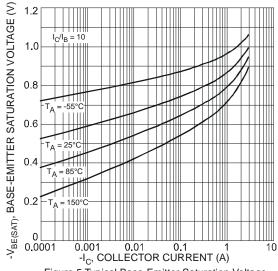


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

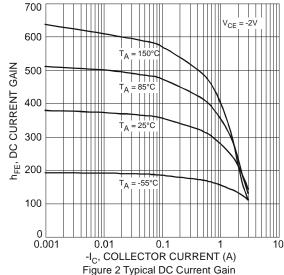
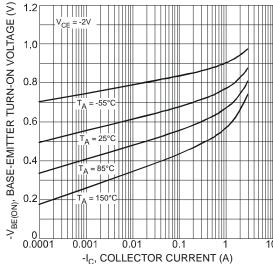


Figure 2 Typical DC Current Gain vs. Collector Current



-I_C, COLLECTOR CURRENT (A) Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

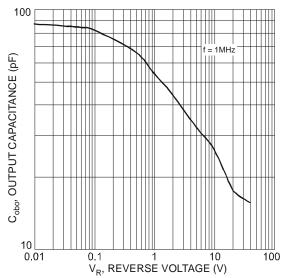
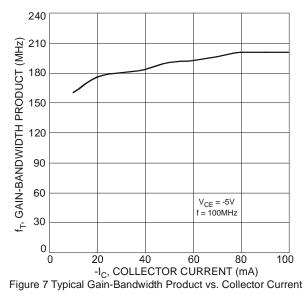


Figure 6 Typical Output Capacitance Characteristics



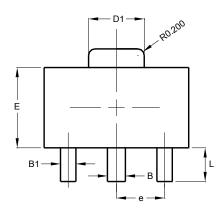


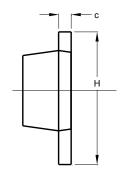


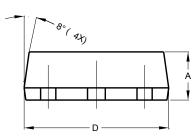
Package Outline Dimensions

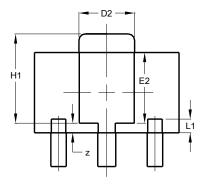
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT89







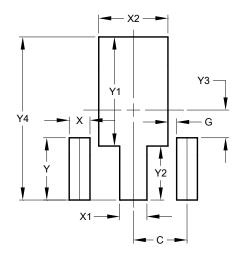


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT89



Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Y	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		



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